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## Real Time Observation of Mechanically Triggered Piezoelectric Current in Individual ZnO Nanobelts

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**Abstract:** The detection of piezoelectric current in one-dimensional semiconductor materials has been a controversial issue due to the possibility of charge annihilation at nanoscale dimensions. We report here, the mechanically triggered electrical current in the uniaxially compressed individual ZnO nanobelts under no applied bias. The measurements were carried out in-situ in a transmission electron microscope. In contrast to the bending mode, the magnitude of the electrical current increased with the increase of uniaxial compression, which indicates load-mode dependency of the detected current. The flow of electrical current through the ZnO nanobelts under applied stress was explained based on the separation of ionic charges along the two ends of the nanobelts due to the applied compressive force. The charge separation is expected to induce an internal electric field inside the nanobelt and facilitates the free charge carriers to move through the nanobelt. Due to the separation and accumulation of charges, the metal-semiconductor system becomes forward biased when contact is established, leading to the flow of electrons through the Schottky barrier.

## 1. Introduction:

The need to develop self-powered nanosystems that can operate wirelessly and independently with a sustainable energy supply has triggered worldwide research on one-dimensional structures with coupled piezoelectricity and conductivity.<sup>1-5</sup> Generally, such nanodevices are fabricated by using individual nanowires/nanotubes/nanobelts having width of 20-100 nm, and few micrometers in length. Quasi-one dimensional nanostructures of ZnO, such as nanowires (NWs) and nanobelts (NBs) exhibit both semiconducting and piezoelectric properties.<sup>6</sup> The coupled piezoelectric and semiconducting properties of the NWs and NBs accommodate charge creation, accumulation, and discharge processes. By deflecting or compressing a NB or NW using a conductive atomic force microscope (AFM)/Nanoindentator (NI) tip, the energy is first created by the deflection/compressive force and stored by piezoelectric potential, and later converts into piezoelectric energy. A piezoelectric effect is required to create electric potential of ionic charges from elastic deformation, and semiconducting property is necessary to separate and maintain the charges and then release the potential via the rectifying behavior of the Schottky barrier at the metal-ZnO interface. Most recently, this approach has been extensively developed to produce usable power output for nanodevices.<sup>3,5</sup>

The recent studies on the piezoresponse of ZnO nanowires show that under bending mode, electrical currents in the range of  $\sim 5$  nA could be detected from a single nanowire.<sup>2,3,5,7</sup> Subsequently, the current increased continuously with the decrease of bending curvature and the current was stabilized at  $\sim 40$  nA. The current dropped immediately when the nanowire was bent again. It was suggested that the piezopotential developed across the thickness of the bent nanowires trapped the free electrons and resulted in decreasing the electrical conductivity.

There is a controversial issue with respect to the detection of piezoelectric signals (sensor mode) in ZnO nanowires. Earlier work of Huston <sup>8</sup> shows that the increase in inherent conductivity of the nanowires can result in reduction of the piezoelectric signal. In this context, Alexe et al. <sup>9</sup> predicted that the detection of piezoelectric signal in bent ZnO nanowires may become a very difficult task when the nanowire has high carrier concentrations and low resistance. They based this prediction on the carrier concentration and mobility data obtained for ZnO nanowires by Sirohi et al. <sup>10</sup>, Alexe et al. <sup>9</sup> concluded that in bent nanowires there was a strong driving force (due to the potential across the nanowire diameter) for the free carriers inside the ZnO NW to travel the shortest way (NW diameter) to cancel the displacive charges. However, Wang <sup>11</sup> has shown out that the detection of piezoelectric signals will be possible for sensitive measurement systems (total capacity <10 pF).

Here, we report the mechanically triggered generation of piezoresponse in the uniaxially compressed piezoelectric ZnO nanobelts. In order to correlate the structure-piezoresponse property of a nanobelt, we conducted structural imaging simultaneously with the piezoresponse measurements inside a TEM with a conducting probe (capacitance < 3 pF). In the present conductive nanoindenter (NI) /TEM system, the force data is read through a proper capacitive force sensor with the resolution close to 100 nN and a maximum force of 10 μN can be applied. <sup>12-14</sup> These nanobelts self-ignite electrically once subjected to an externally applied uniaxial compressive load without any external bias. It should be noted that nanobelts with lengths shorter than ~1-2 μm were used in this study to ensure pure compression without bulking and bending of the nanobelts. <sup>15</sup>

## 2. Experimental Procedure:

The piezoresponse experiments on ZnO nanobelts were conducted in situ in a high resolution TEM using a special NI holder. All the measurements were carried out on a single tilt NI holder in a JEM 4000FX TEM, operated at 200 KeV. The detailed description of NI-TEM holder is reported earlier in our study on mechanics of ZnO nanowires.<sup>16</sup> The electrochemically etched gold wire with ZnO nanobelts that were attached to the gold tip by conducting silver (Ag) paste was mounted to the piezo-driven movable part of the holder facing the fixed and sharp NI tip. The first step when using the NI-TEM setup is to calibrate the electrical conversion factor ( $C$ ) of the force sensor. This constant is related to the electrical sensitivity of each sensor and must be set to a value that triggers a 1:1 correspondence of the  $F-d$  (Force-displacement) relation when the cantilever is tested against the bare substrate of gold. In the present NI system it is  $1.01pF/0.1\mu N$ . In such an arrangement, atomic scale imaging and  $F-d$  measurements are carried out concurrently.

The ZnO nanobelts used in our study are grown in a double quartz tube configuration thermal chemical vapor deposition (CVD) system as reported previously but without the use of Au catalyst.<sup>17</sup> The growth was performed in a horizontal furnace consisting of a quartz tube vacuum chamber. A closed end smaller quartz tube (60 cm long and 2 cm in diameter) containing the precursor materials and the substrates was inserted within the vacuum chamber. A mixture of ZnO (0.2 g) and graphite (0.1 g) powder in an alumina boat was used as the precursor materials. The boat is placed at the closed end of the smaller quartz tube. A series of low resistance silicon substrates (1–4) was then placed downstream from the mixture in the small quartz tube with a

2 cm spacing in between. Substrate 1 and 4 are 20 cm and 26 cm away from the boat, respectively. Once, inserted the closed end of smaller quartz tube is in the hottest zone of the furnace. The temperature of the furnace was raised to 1100 °C. The substrates were in a temperature zone of ~650 to 450 °C. At ~350 °C, oxygen gas was introduced into the furnace at a 10 sccm flow rate. The temperature was held at 1100 °C for 30 minutes and turned off to allow cooling to 600–700 °C in ~1 hour. Experiment was stopped by switching off the furnace and allowing the system to cool down to room temperature. ZnO NBs were obtained at substrates 1 and 2.<sup>17</sup>

### 3. In-Situ Observation of Piezoelectric Current

The ZnO nanobelt was examined in situ under high-resolution transmission electron microscope before the mechanical straining. The length of the suspension part of the nanobelt was ~2 μm. The width of the nanobelt was measured to be 400 nm (Fig. 1a) and the aspect ratio was estimated to be 8. The TEM analysis revealed the single crystal structure of the ZnO nanobelt and the growth direction was along [0001] as evident by the high-resolution lattice image (Fig. 1b) and the corresponding diffraction pattern (inset Fig. 1b).

To ensure the reliability of the recorded data, it is important that nanobelt be firmly attached to the tip of the gold wire (250 μm diameter) mounted on the piezotube. To ensure this, the nanobelt was attached to the gold tip by silver paste. In order to achieve a good electrical contact between the ZnO nanobelt and the tungsten tip, a field emission process was introduced at the first stage to clean the nanobelt tip and welding the connection. During the field emission, the ZnO nanobelt was kept ~ 0.5 μm away from the tungsten surface, where 20 V was applied. Under this condition, the emission current could reach 17 nA. After 1 minute of emission, the

high voltage was turned off and the ZnO nanobelt was quickly moved towards the Au tip surface to make a contact. We have repeated this process several times and found that it is very effective for making a reliable electrical contact, possibly due to the high temperature generated at the tip by the emission process as well as desorption of the surface contamination. During the loading and unloading cycles, no slippage at the both ends of the nanobelt was observed.

It is to be noted that to get effective current generation, the metal–nanobelt contact is required to be Schottky in nature. The choice of Au electrodes served as contacts for the current measurements is justified by the Schottky–Mott model, which predicts that metals with high work functions are key candidates for rectifying contacts for *n*-type semiconductors. Hence, the materials of choice are limited to gold, platinum, and palladium.<sup>18</sup>

Fig. 2a shows the contact of a nanobelt with the NI tip in an uncompressed state. The ZnO nanobelt was moved against NI tip by the incremental movement of the piezodriven gold tip. As the ZnO nanobelt was strained, a few regions on the nanobelt showed local bright field contrast. The local changes observed in contrast may be related to atomic distortion resulting from stress concentration. Fig. 2b shows the nanobelt under slightly compressive state (strain,  $\epsilon_1 \sim 5\%$ ) and the state of the nanobelt with strain,  $\epsilon_2 \sim 10\%$  is shown in Fig. 2c. The nanobelt in the highest compression state ( $\epsilon_3 \sim 25\%$ ) is shown in Fig. 2d.

The corresponding current variation versus time (*I*-*t*) during compression and uncompressed states in single ZnO nanobelts are shown in Fig. 3a-c. In this measurement, there was no applied bias voltage in the system and the current was continuously recorded while the ZnO nanobelt was slowly compressed against the NI tip. The magnitude of the applied forces is plotted as the dash lines in Fig. 3a-c. As evident in Fig. 3a-c, when the NI tip contacts the nanobelt, the current is almost zero. As the nanobelt is compressed against the NI tip (Region I),

there is a continuous increase in the current. When the nanobelt was under 25 % compression, the current reached to a maximum value of 175.34 nA. During the unloading stage (Region II), the current again slowly drops to almost zero with decrease in the compression along the length of the nanobelt. This detected current is expected to be the result of piezoelectric potential generated in the nanobelts. We tested several nanobelts in the compression mode and observed the similar behavior of generation piezocurrent with time. Another such observation for a nanobelt of width ~ 200 nm and length ~ 1 μm is shown in Fig. 3b, where the nanobelt shows the electric current of 67.4 nA under the maximum compression. The behavior of piezoelectric current is consistent with the data reported by Sridhar et al.<sup>19</sup> on the current generated during the indentation of PZT-4 and (Ba<sub>0.917</sub>Ca<sub>0.083</sub>) TiO<sub>3</sub> piezoelectric materials. One should note that the charge induced by the mechanical compression is due to the strained contact area and will not be sustained if the contact area is fixed.<sup>19</sup> However, in the case of an advancing contact (i.e., increasing load), the charge buildup increases due to the increase in strained area. Hence, the observed piezoelectric current from ZnO nanobelt in the present investigation is not transient. If the indenter is conducting and is grounded, a charge opposing that of the specimen would develop. The dynamic change in the charge at the indenter needed to sustain charge neutrality can be measured as a quasi-static current. [In one of the recent study<sup>20</sup>, the piezoelectric coefficient from the ZnO nanowires was measured on the basis of the direct linear piezoelectric response from the substrate integrated ZnO nanowire array devices on galvanized steel.](#)

In order to check the irradiation effect of the electron beam on the piezocurrent, we measured the current versus time of a ZnO nanobelt without electron beam. We found that there was no change in the value of current with and without beam as shown in Fig. 3b & 3c. Fig. 3b is the I-t curve with the beam on and Fig. 3c is the corresponding I-t curve with beam off for the



same nanobelt of width  $\sim 200$  nm. However, we found that there is less fluctuation of piezocurrent without electron beam as shown in Fig. 3c.

Similar experiment on the observation of current by mechanical stress was conducted on Si nanowire to further clarify that if the detected electrical current is exclusive to ZnO nanobelts. However, the compression of Si nanowire did not generate any current in opposite to what we had observed for the case of ZnO nanobelts. The current versus time plot of Si nanowire is shown in Fig. 3d. The Si nanowire is a non-piezoelectric material, hence did not produce any current upon compression. This again indicates that the possibility for the TEM electron beam to be transported through the nanowire and detected by the current measurement setup cannot be the case. The experiment on Si nanowires clarifies that the electrical current observed in ZnO nanobelts under mechanical stressing is due to piezoelectricity.

The high-resolution image before the ZnO nanobelt touches the NI tip (Fig. 4a) clearly shows the diffraction contrast at the top of the nanobelt is due to the presence of some dislocation, probably due to mechanical stress when the nanobelt was harvested from the substrate. From the low magnification image, the major part of the nanobelt appears to be free from any defects. The nanobelt in a compressed state (Fig. 4b) shows high bright field diffraction contrast, resulting from atomic distortion due to the high strain field. The high resolution image of the nanobelt at the initial state, i.e before the compression shows highly crystalline and continuous straight fringes (Fig. 4c), however after high compression, some regions of the nanobelt shows discontinuity of fringes (Fig. 4d) over the few atomic layers (surrounded by red rectangles), which indicates that there is creation of planar defect due to high compression and also at some point, there is broadening of lattice fringes (some of them are indicated by blue arrow), which might occur due to the creation of point defect. The above observation is also

confirmed by the corresponding fast Fourier transform (FFT) patterns. The FFT pattern of the nanobelt in the relaxed state shows sharp and intense diffraction spots (inset of Fig. 4c), however the FFT pattern corresponding to the compressed state shows the diffuse diffraction spots (inset of Fig. 4d), which indicates the presence of planar defect. The formation of defects upon bending of the nanobelt/nanowire has also been reported earlier for ZnO nanowires<sup>21, 22</sup> and also for other ceramic and oxide nanowires like SiC, SiO<sub>2</sub> etc.<sup>23, 24</sup> These kinds of planar defects and point defect can alter the electronic structure by producing the localized resonant states.<sup>25</sup>

#### 4. Load Mode Dependency of the Electrical Potential

Previous studies on the in-situ electromechanical behavior of ZnO nanowires/nanobelts have shown that the electrical conductivity of ZnO nanowire/nanobelt decreases upon elastic bending.<sup>7, 26-29</sup> However, we observed that the magnitude of electrical current in ZnO nanobelts increases with the increase in applied compressive stress. As observed in Fig. 3a, the current increases to its maximum value (~175.34 nA) under the compression mode with the applied load of ~9.98  $\mu$ N. It should be noted that our ZnO nanobelts are short (~1-2  $\mu$ m) as compared to the previously studied ZnO nanowire/nanobelts (~10-20  $\mu$ m)<sup>30, 31</sup>, and therefore compression of such nanobelts did not form physical bending on the nanobelt but rather uniaxial compression.

The effect of loading mode on the output piezoelectric signal can be explained by taking into account the effect of deformation modes on the separation of positive and negative ionic charges (Zn<sup>2+</sup> and O<sup>2-</sup>).

A piezoelectric material responds to the applied mechanical force by the displacive motion of (+) and (-) charges (Zn<sup>2+</sup> and O<sup>2-</sup>) to form a dipole. To better understand the electric potential development in our nanobelts, a series of finite element modeling was performed using

COMSOL Multiphysics 4.0A. Zinc oxide nanobelts were modeled as an elastic piezoelectric material with growth along [0001] direction. Free tetrahedral element was used for meshing the structure. Elastic constant tensor,  $C$ , piezoelectric coefficient tensor,  $e$ , and dielectric constants tensor,  $\kappa$ , are defined as follows by equation (1), (2) and (3):

$$C = \begin{bmatrix} 207 & 117.7 & 106.1 & 0 & 0 & 0 \\ 117.7 & 207 & 106.1 & 0 & 0 & 0 \\ 106.1 & 106.1 & 209.5 & 0 & 0 & 0 \\ 0 & 0 & 0 & 44.8 & 0 & 0 \\ 0 & 0 & 0 & 0 & 44.8 & 0 \\ 0 & 0 & 0 & 0 & 0 & 44.6 \end{bmatrix} [GPa] \quad (1)$$

$$e = \begin{bmatrix} 0 & 0 & 0 & 0 & -0.45 & 0 \\ 0 & 0 & 0 & -0.45 & 0 & 0 \\ -0.51 & -0.51 & 1.22 & 0 & 0 & 0 \end{bmatrix} [C/m^2] \quad (2)$$

$$\kappa = \begin{bmatrix} 7.77 & 0 & 0 \\ 0 & 7.77 & 0 \\ 0 & 0 & 8.91 \end{bmatrix} \cdot \varepsilon_0 \quad (3)$$

Where,  $\varepsilon_0 = 8.85 \times 10^{-12}$  F/m is the vacuum permittivity. In this model, force was applied at one end, while the other end was assumed to be fixed and electrically grounded. Two loading cases were considered: Figs. 5(a-c) correspond to the uniaxial compression and Figs. 5(d-f) describe the bending scenario. Figs. 5(a-c) show the displacement,  $d$ , axial strain,  $\varepsilon$ , and the corresponding electrical potential,  $V$ , of a ZnO nanobelt under the uniaxial compressive loading,  $F$ . Under the uniaxial compression, strain,  $\varepsilon$ , is developed along the length of the ZnO nanobelt separating the anions ( $Zn^{2+}$ ) and cations ( $O^{2-}$ ) in ZnO and polarize it along the straining direction (shown in Fig. 5c). The polarization can be given by  $P = \varepsilon e_{33}$ , where  $e_{33}$  is the piezoelectric tensor.<sup>32, 33</sup> This

polarization produces a potential drop of  $V^+$  ( $V > 0$ ) –  $V^-$  ( $V < 0$ ) =  $|\epsilon| L e_{33}$  along the length  $L$  of the nanobelt.

The modeling results including displacement, strain, and electrical potential for the bending case are shown in Figs. 5(d-f). There is clear difference in terms of strain and electrical potential distribution between the two loading scenarios. In the bent NB, tensile and compressive strains formation results in creation of positive and negative electrical potentials on the outer and inner surfaces, respectively. The modeling results are in agreement with the previous studies on the detection of positive and negative charges on the tension and compressive sides of ZnO nanowires.<sup>34</sup> These ionic charges form an electric field along the width (perpendicular to the axial direction) of the nanobelt, which can trap the free charge carriers and therefore reduce the electrical conductivity. However, under uniaxial compression, the charge separation along the axial direction of the nanobelt can induce an internal electric field inside the nanobelt that assists the movement of charge carrier through the nanobelt resulting in an improvement in electrical conductivity.

The schematic diagram of the model to describe the two mechanisms is shown in Fig. 6. Initially in the piezoelectric material, (+) and (-) charges form a dipole with slight separation from the center of the dipole (Fig. 6a). When the piezoelectric nanobelt is bent, the charges are separated along the thickness of the nanobelt. The positive charges will be accumulated along the outer arc surface (tension side) and negative charges along the inner arc surface (compressed side). The electric field,  $E$ , is generated perpendicular to the length of the nanobelt, and hence perpendicular to the flow of charges. The electrons are trapped in this configuration (Fig. 6b). In the uniaxial compression case, the ionic charges will be separated along the length of the nanowire/nanobelt and form an electric field in the carrier movement direction that gives the

driving force for the flow of electrons (Fig. 6c). By the increase of the applied force, more charges will be displaced and hence the magnitude of the electric field increases. Therefore, the magnitude of the detected piezo-current increases by the increase of the applied axial force. The increase in piezoelectric current with time as depicted in Fig. 3 is also due to the increase in the contact area between the NI tip and the nanobelt, when the nanobelt is under the increasing compressive stress.

Our results on ZnO nanobelts are in agreement with that of reported by Shreedhar et al.<sup>20</sup> on PZT and  $(\text{Ba}_{0.917}\text{Ca}_{0.083})\text{TiO}_3$  materials, which shows that when a piezoelectric material is indented towards the poling direction, the induced current increases in magnitude with time, first rapidly and then slowly. This increase is to be expected since the contact area increases with time. The induced current is a result of the electrically polarized contact area.

The piezoresponse observed in nanobelts in our study is explained by linear piezoelectric equations as reported by Giannakopoulos and Shreedhar et al.<sup>35, 20</sup> It is mentioned that mechanical displacement induces a polarization on the piezoelectric specimen at the contact area. By integrating the electric charge distribution under the indenter, an expression for the mechanically induced total charge,  $Q$ , is found as

$$Q = \frac{16}{3} M_1 \frac{a^3}{D} + 2\pi a \left[ \phi_0 M_2 - M_1 \left( h - \frac{2a^2}{D} \right) \right] \quad (4)$$

The charge distribution (equation 4) under the indenter is due to the strained contact area and will not be sustained if the contact area is fixed. However, in the case of an advancing contact ~i.e., spherical indentation with increasing load, the charge buildup increases due to the increase in strained area. If the indenter is conducting and is grounded, a charge opposing that of the specimen would develop. The dynamic change in the charge at the indenter needed to sustain

charge neutrality can be measured as a quasi-static current. The constants  $M_1$  and  $M_2$  depend in a complicated way on the five elastic ( $c_{ij}^E$ ), two dielectric ( $\epsilon_{ij}^T$ ), and three piezoelectric ( $e_{ij}$ ) constants that characterize the material.<sup>35, 20</sup> The parameters,  $\phi$  is an electric potential,  $a$  is the contact radius and  $h$  is the displacement corresponding to the rigid sphere of diameter  $D$ .

It is to be noted that the piezoelectric current would not increase infinitely with the increasing compressive stress. Increase of compressive stress beyond some threshold value will induce mechanical instability in the nanowires, which eventually may result in fracture. Therefore, the magnitude of stress was kept in linear regime.

### 5. Contact Resistance and the Detection of Piezoelectric Current

The Schottky contact between the metal and semiconductor (M-S) ZnO nanobelt is one of the key factors that can affect the detection of piezo-current signal. Schottky barriers can form at metal-semiconductor (M-S) interfaces. According to the configuration of both metallic contacts and the ZnO NB, it can be considered that the piezoelectric current produced by the compression of ZnO nanobelt flows through a M-S-M (Metal-Semiconductor-Metal) circuit. One of the contacts is Schottky and is formed between the conductive NI tip (Au coated) and ZnO nanobelt ( $n$  type semiconductor) and the other is Ohmic formed between Ag paste and the ZnO nanobelt. The nonlinear current-voltage (I-V) behavior is predicted if both the contacts are Schottky-type however, we have observed a nonlinear I-V behavior from the ZnO nanobelt, even if one contact is Schottky and the other is Ohmic. The reason for this barrier can be the interface layer or surface layer of ZnO at the contact.

As predicted by the simulation, when the ZnO nanobelt was subjected to uniaxial compression (Figs. 5a-c), the ionic charges will be separated along the axial length of the nanobelt and form a polarized electric field in the direction of carrier movements in the M-S-M

circuit. Schematic representation of the process with corresponding band structure is shown in Figs. 7(a, b). Fig. 7(a) shows the uncompressed ZnO nanobelt with one end grounded and the other end to be pushed against a conducting NI tip. The corresponding band structure diagram illustrates the formation of the Schottky barrier  $\phi_{\text{Au-NB}}$  at the metal (Au tip)-n type semiconductor (ZnO nanobelt) contact, and an Ohmic contact at the metal Ag - n type semiconductor interface. Fig. 7(b) depicts the ZnO nanobelt in a compressed state. In a compressed state there will be separation of charges and the Schottky barrier i.e  $\phi_{\text{Au-NB}}$  can become forward biased when the (-) charges accumulate at the STM tip and ZnO nanobelt interface. The electrons will flow easily through the Ohmic contact formed between (Ag) - n type semiconductor completing the M-S-M circuit. Similar observation of flow of current through forward biased Schottky diode has been reported by Wang et al. <sup>2</sup> for the bending of ZnO nanowire by in-situ AFM experiments.

The Schottky barrier height can also be modulated under mechanical straining. <sup>36-40</sup> This relationship can be defined as [in equation \(5\) below](#)

$$\ln [I(\varepsilon)/I(0)] = -\Delta\phi/kT \quad (5)$$

Where  $I(\varepsilon)$  and  $I(0)$  are the current measured through the ZnO nanowire at a fixed bias with and without being strained, respectively. This indicates that the change of Schottky barrier height,  $\Delta\phi$ , has an approximately linear relationship with strain. From the above argument, we can conclude that the Schottky barrier height can be reduced due to the straining of the ZnO nanowire and this further assists the flow of electrons through the M-S-M circuit.

In many reported studies on piezoelectric behavior of ZnO nanostructures, PVP and PZT material <sup>2, 3, 5, 7, 26-29, 41, 42</sup>, the piezoelectric charges manifest themselves as a transient of current.

This is true when the piezoelectric materials are introduced with periodical on-off strains as reported by Chang et al.<sup>41</sup>, Chen et al.<sup>42</sup> and Zhang et al.<sup>26-29</sup> Going through the above mentioned studies, we have found that the strains applied on the ZnO nanowires, PVP and PZT materials are periodic and thus lead to transient flow of piezocurrent in response to the on-off strains. This is clearly different from our case. In our experimental work, we observed an increasing piezoelectric current when the ZnO nanobelt was under an increasing strain at a constant rate. We then observed a decreasing piezoelectric current when we release the strain at a constant rate. Our detected current is following the magnitude of the applied strain since forces are always applied and piezo-potential is always present as a result of charge separation in a piezoelectric material.

It is to be noted that we have taken enough care to minimize the irradiation effects of electron beam on the generation of piezocurrent in our present study in ZnO nanobelt. We made efforts to eliminate the effect of electron beam by conducting the structural characterization at a low beam current of 2.91 nA and study the piezoelectric current at even lower beam current of 0.72 nA. The low beam current of 0.72 nA and 2.91 nA was obtained by adjusting the possible combination of condenser aperture and spot size. The electron beam was spread to avoid any convergence of the beam on the sample. In addition, we shut off the electron beam while recording I-V data. Thus the related contamination and electron beam induced effect on piezocurrent is decently minimized. Similar concerns about the effect of electron beam have also been reported by Bai et al.<sup>43</sup> and Han et al.<sup>44</sup> Han et al. carried out similar in situ experiment at 200kV and with a low beam current and found through simple calculation<sup>45</sup> that the local temperature is no more than a few degrees above the room temperature. We did not observe any appreciable change in I-V data after repeating the cycles few times and it proves that the



nanobelt is not affected by the electron beam during the time it is under the electron beam for manipulation and I-V acquisition. In some of our previous work<sup>15</sup>, the low current beam radiation did not induce any detectable change in the conductivity of the nanobelts indicating that the effect of electron beam can be ignored in the analysis of the data presented in this work.

## Conclusion

In conclusion, under no external bias piezoelectric current could be generated in a single ZnO nanobelt by mechanically compressing it using a conductive force probing system. The mechanically triggered electrical response increases with the increase in the uniaxial compressive deformation. The mechanism behind this observation of piezoresponse under compressive stress is due to the separation of ionic charges ( $\text{Zn}^{2+}$  and  $\text{O}^{2-}$ ) along the stress axis. This charge separation leads to the generation of electric field inside the nanobelt and assists the carrier charges to move through the nanobelt without any external bias. Due to the separation and accumulation of charges at the metal-ZnO nanobelt end, one of the metal-semiconductor contacts becomes forward biased, leading to the flow of electrons through the barrier. The increase of applied compressive force will further separate the charges and increases the polarization potential. This will increase the electric field and hence the driving force for the flow of free charge carriers. The increase in piezoelectric current with time can also be mediated with the increase in the contact area between the nanoindenter tip and the nanobelt, when the nanobelt is under the increasing compressive stress.

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**References:**

- [1] U. Ozgur, Y. I. Alivov, C. Liu, A. Teke, M. A. Reshchikov, S. Dogan, V. Avrutin, S. J. Cho, H. Morkoc, *J. Appl. Phys.*, 2005, **98**, 041301.
- [2] Z.L. Wang, *Adv. Funct. Mater.*, 2008, **18**, 3553.
- [3] J. Zhou, P. Fei, Yifan Gao, Y. Gu, J. Liu, G. Bao, Z. L. Wang, *Nano Lett.*, 2008, **8**, 2725.
- [4] S. Xu, Y. Qin, C. Xu, Y. Wei, R. Yang, Z. L. Wang, *Nature Nanotechnol.*, 2010, **5**, 366.
- [5] X. Wang, J. Zhou, J. Song, J. Liu, N. Xu, Z. L. Wang, *Nano Letts.*, 2006, **6**, 2768.
- [6] Z. L. Wang, *J. Phys.: Condens. Matter*, 2004, **4**, 423.
- [7] S. Yang, L. Wang, X. Tian, Z. Xu, W. Wang, X. Bai and E. Wang, *Adv. Mater.*, 2012, **24**, 4676.
- [8] A. R. Hutson, *Phys. Rev. Lett.*, 1960, **4**, 505.
- [9] M. Alexe, S. Senz, M. A. Schubert, D. Hesse and U. Gosele, *Adv. Mater.*, 2008, **20**, 4021.
- [10] J. Sirohi, I. Chopra, *J. Intell. Mater. Syst. Struct.*, 2000, **11**, 246.
- [11] Z. L. Wang, *Adv. Mater.*, 2009, **27**, 1311.
- [12] M. A. Wall, U. Dahmen, *Microsc. Res. Tech.*, 1998, **42**, 248.
- [13] E. A. Stach, T. Freeman, A. M. Minor, D. K. Owen, J. Cumings, M. A. Wall, T. Chraska, R. Hull, J.W. Morris, Jr A. Zettl, U. Dahmen. *Microsc. Microanal.* 2001, **7**, 507.
- [14] A. M. Minor, J.W. Morris, E.A. Stach, *Appl. Phys. Lett.* 2001, **79**, 1625.
- [15] A. Asthana, K. Momeni, A. Prasad, Y. K. Yap, R. S. Yassar,; *Appl. Phys. Lett.*, 2009, **25**, 172106.
- [16] A. Asthana, K. Momeni, A. Prasad, Y. K. Yap and R. S. Yassar, *Nanotechnology* , 2011, **22**, 265712.
- [17] S. L. Mensah, V. K. Kayastha, Y. K. Yap. *J. Phys. Chem. C*, 2007, **111**, 16092.
- [18] B. J. Coppa, C. C. Fulton, S. M. Kiesel, R. F. Davis, C. Pandarinath, J. E. Burnette, R. J. Nemanich, D. J. Smith, *J. Appl. Phys.*, 2005, **97**, 103517.
- [19] S. Sridhar, A. E. Giannakopoulos, S. Suresh, and U. Ramamurty, *J. Appl. Phys.*, 85 (1999), 380.

- [20] J. M. Velazquez, S. Baskaran, A. V. Gaikwad, T. Ngo-Duc, X. He, M. M. Oye, M. Meyyappan, T. K. Rout, J. Y. Fu, and S. Banerjee, *Appl. Mater. Interfaces* 2013, **5**, 10650–10657
- [21] H. Xiaobing, J. Guangyin, Z. Xinzheng, M. Renmin, S. Xuefeng, X. Jun, L. Zhimin, W. Ning, Y. Dapeng, *Nano Res.* 2009, **2**, 553.
- [22] Y. Ding, Z. L. Wang, *J. Phys. Chem. B*, 2004, **108**, 12280.
- [23] X. D. Han, Y. F. Zhang, K. Zheng, Z. Zhang, Y. J. Hao, X. Y. Guo, J. Yuan, Z. L. Wang, *Nano Lett.* 2007, **7**, 452.
- [24] K. Zheng, X. Han, L. Wang, Y. Zhang, Y. Yue, Y. Qin, X. Zhang, Z. Zhang, *Nano Lett.*, 2009, **9**, 2471.
- [25] W. A. de Heer, J. –M. Bonard, K. Fauth, A. Chatelain, L. Forro, D. Ugarte, *Adv. Mater.*, 1997, **9**, 87.
- [26] K. H. Liu, P. Gao, Z. Xu, X. D. Bai and E. G. Wang, *Appl. Phys. Letts.*, 2008, **92**, 213105.
- [27] Y. Liu, Z. Y. Zhang, Y. F. Hu, C. H. Jin and L -M Peng, *J. Nano Sci. Nanotechnol.*, 2007, **8**, 1.
- [28] X. Lin, X. B. He, T. Z. Yang, W. Gao, D. X. Shi, H. –J Gao, D. D. D. Ma, S. T. Lee, F. Liu and X. C. Xie, *Appl. Phys. Letts.*, 2006, **89**, 043103.
- [29] P. M. F. J. Costa, D. Goldberg, G. Shen, M. Mitome, and Y. Bando. *J. Mater. Sci.*, 2008, **43**, 1460.
- [30] M. Huang, P. Rugheimer, M. G. Lagally, and F. Liu, *Phys. Rev. B*, 2005, **72**, 085450.
- [31] Q. H. Li, Q. Wan, Y. X. Liang, and T. H. Wang, *Appl. Phys. Letts.*, 2004, **84**, 4556.
- [32] M. H. Zhao, Z. L. Wang, S. X. Mao, *Nano Letts.*, 2004, **4**, 587.
- [33] J. F. Nye, *Physical Properties of Crystal*; Oxford University Press: London, 1957.
- [34] J. Zhou, P. Fei, Y. Gao, Y. Gu, J. Liu, G. Bao, Z. L. Wang, *Nano Letts.*, 2008, **8**, 2725.
- [35] A.E. Giannakopoulos and S. Suresh, *Acta Materialia*, 1999, **47**, 2153.
- [36] J. Appenzeller, M. Radosavljevic, J. Knoch, Ph. Avouris, *Phys. Rev. Letts.*, 2004, **92**, 048301.

- [37] J. Zhou, Y. Gu, P. Fei, W. Mai, Y. Gao, R. Yang, G. Bao, Z. L. Wang, *Nano Letts.*, 2008, **8**, 3035.
- [38] Y. Liu, Z. Kauser, P. P. Ruden, Z. Hassan, Y. C. Lee, S. S. Ng, F. K. Yam, *Appl. Phys. Letts.*, 2006, **88**, 022109.
- [39] W. Shan, M. F. Li, P. Y. Yu, W. L. Hansen, W. Walukiewicz, *Appl. Phys. Letts.*, 1988, **53**, 974.
- [40] K. W. Chung, Z. Wang, J. C. Costa, F. Wiliamson, P. P. Ruden, M. I. Nathan, *Appl. Phys. Letts.*, 1991, **59**, 1191.
- [41] C. Chang, V. H. Tran , J. Wang, Y-K. Fuh and L. Lin, *Nano Lett.*, 2010, **10**, 726.
- [42] Xi Chen, Shiyou Xu , Nan Yao, and Yong Shi *Nano Lett.*, 2010, **10**, 2133.
- [43] X. D. Bai, D. Goldberg, Y. Bando, C. Y. Zhi, C. C. Tang, M. Mitome and K. Kurashima, *Nano Lett.*, 2007, **7**, 632.
- [44] X. D. Han, Y. F. Zhang, K. Zheng, X. N. Zhang, Z. Zhang, Y. J. Hao, X. Y. Guo, J. Yuan and Z. L. Wang. *Nano Lett.*, 2007, **7**, 4529.
- [45] I. Jencic, M. W. Bench and I. M. Robertson, *J. of Appl. Phys.*, 78, 974 (1995).

### Figure Captions:

Fig. 1: (a) The bright field TEM image of a ZnO nanobelt attached firmly to the gold wire and approaches the nanoindenter tip; and (b) The high-resolution TEM image and the corresponding diffraction pattern of the ZnO nanobelt.

Fig. 2: (a) The bright field TEM image of a ZnO nanobelt in contact with the gold wire and nanoindenter tip. (b), (c) & (d) The nanobelt was subjected to progressive axial force exerted by the incremental movement of the gold wire against the NI tip.

Fig. 3: (a-c) The piezocurrent variation with time during the loading (Region I) and unloading (Region II) of three ZnO nanobelts. All the ZnO nanobelts have similar length but different width dimension: (a) width of  $\sim 400$  nm, (b) width of  $\sim 200$  nm, and (c) width of  $\sim 200$  nm with no electron beam. (d) The current variation with time during the loading and unloading of a Si nanowire under loading and unloading.

Fig. 4: The high resolution TEM image (a) before the nanobelt contacts the nanoindenter tip, and (b) the same nanobelt under a highly compressive state. Lattice imaging of the nanobelt corresponding to the (c) undeformed state, and (d) highly compressive state is shown.

Fig. 5: Finite element simulation of a ZnO NB subjected to (a-c) uniaxial compression and (d-f) cantilever bending: (a and d) displacement contours, (b and e) strain contours, and (c and f) electrical potential contours along the length of the nanobelt are shown.

Fig. 6: The schematic diagram of model depicts (a) the initial state of the piezoelectric material; (b) the state of a bent nanobelt; and (c) the state of compressed nanobelt.

Fig. 7: The schematic diagram of a (a) uncompressed ZnO nanobelt with one end grounded and the other end to be pushed against a conducting NI tip. The band structure diagram shows the formation of the Schottky barrier at the metal (Au tip) - n type semiconductor (ZnO nanobelt) and an Ohmic contact at metal Ag - ZnO nanobelt; and (b) a ZnO nanobelt in the compressed state. The band diagram illustrates that one of the Schottky barriers is forward biased and the electrons flow through the barrier.

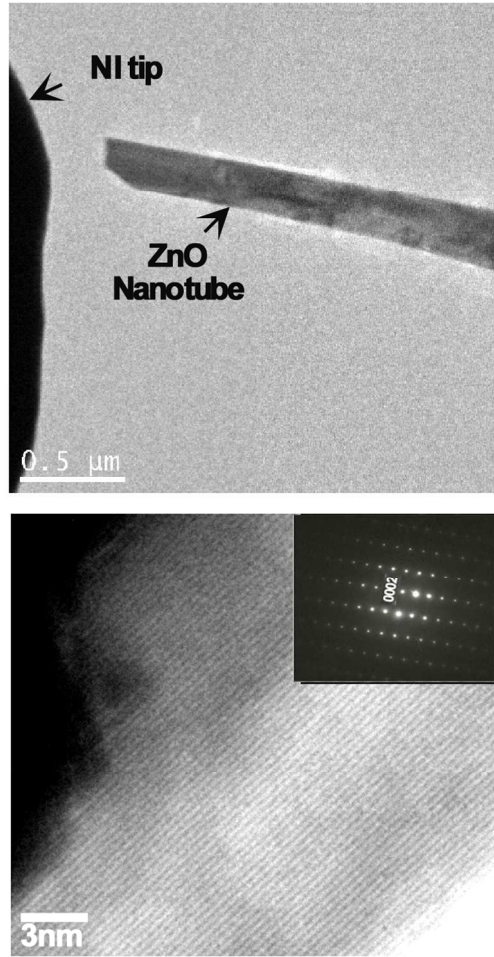
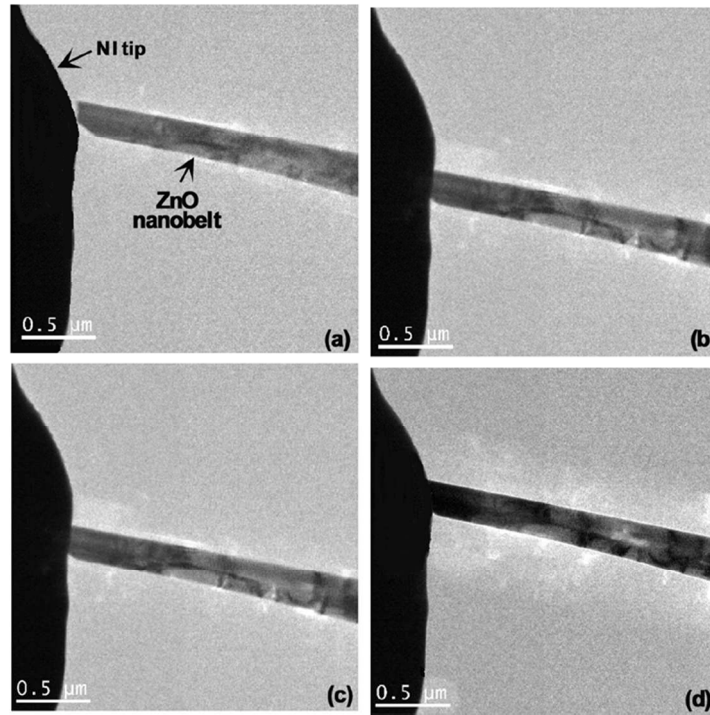


Fig. 1

**Fig. 2**

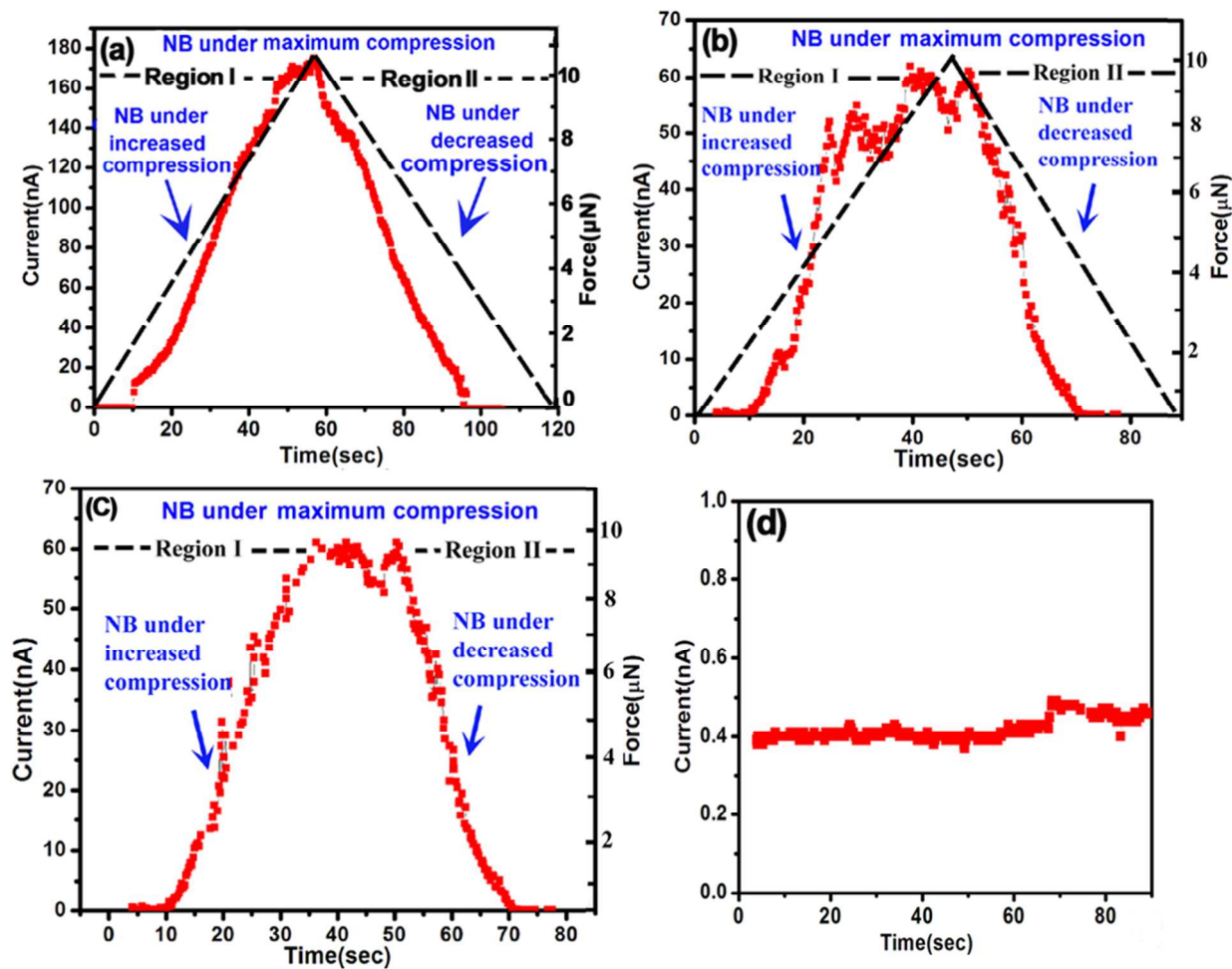


Fig. 3



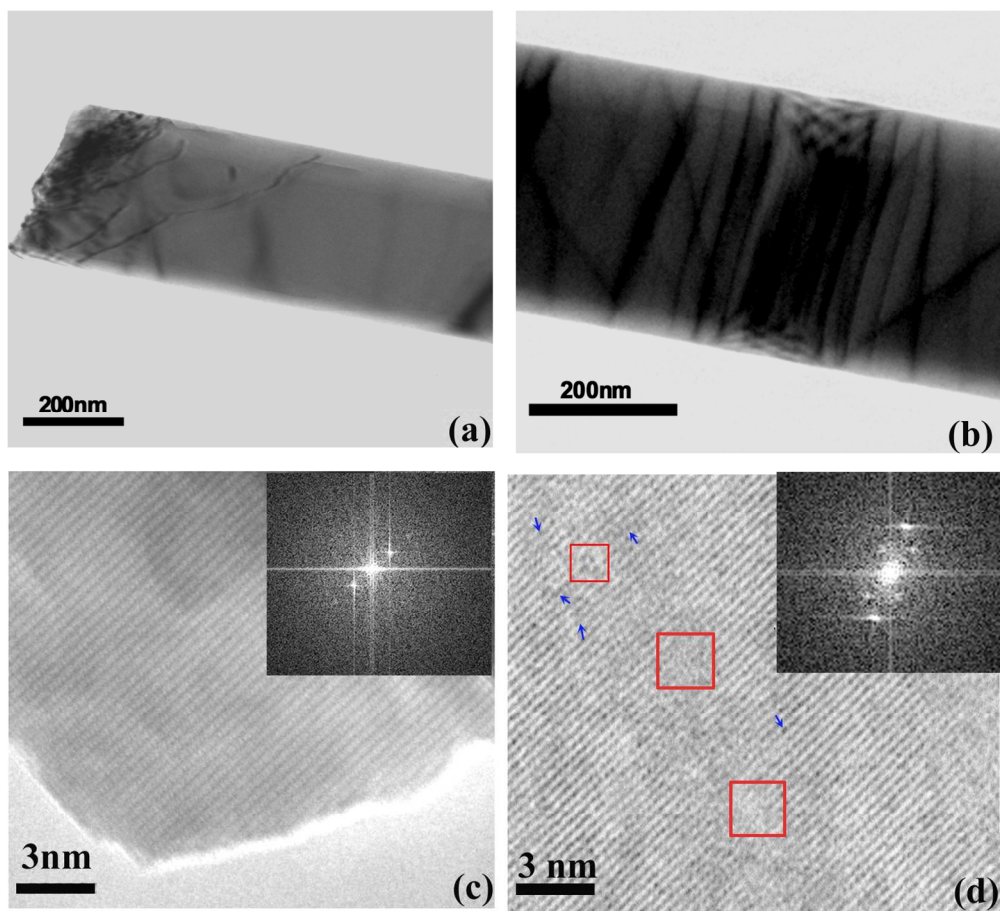


Fig. 4

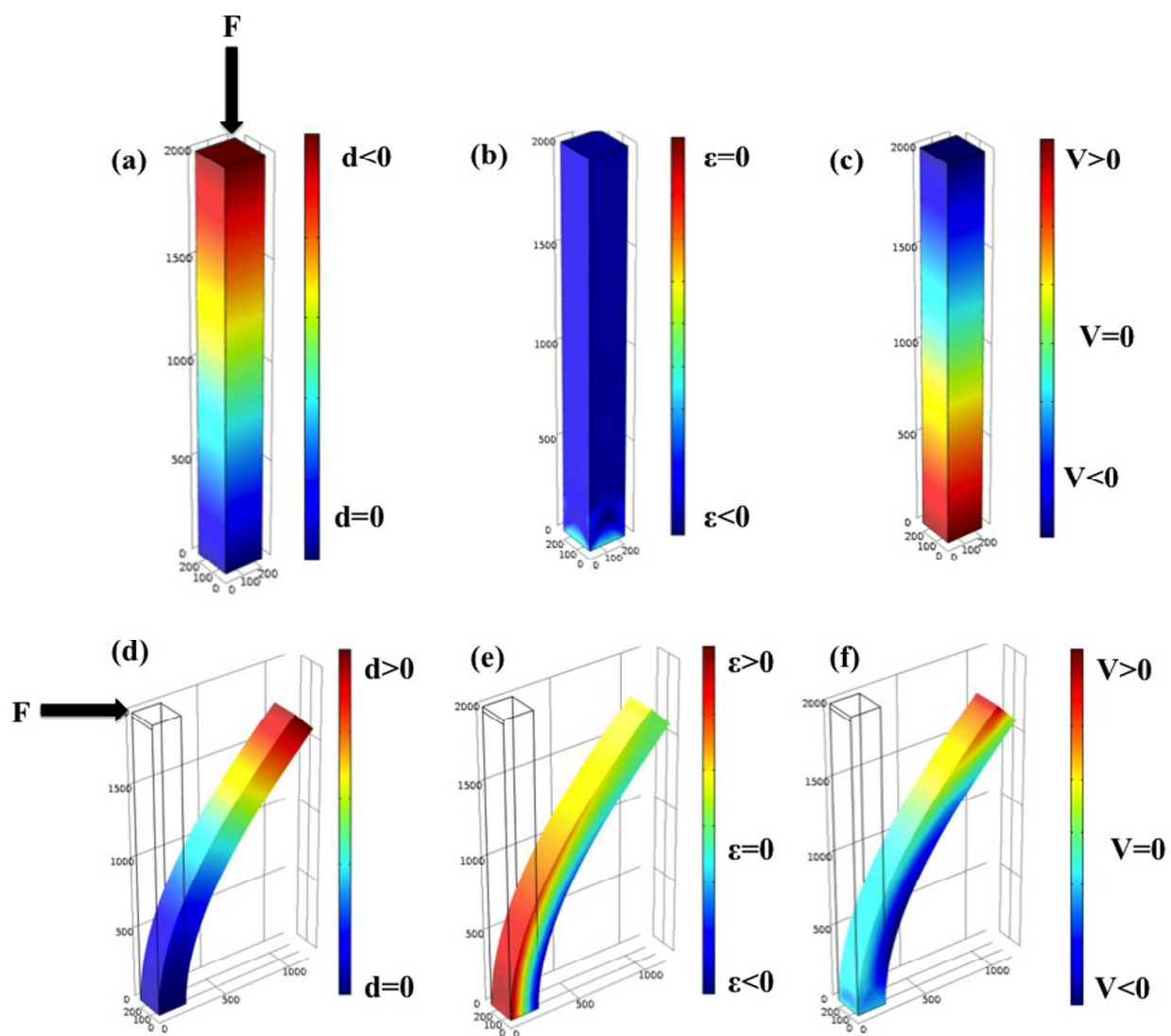


Fig. 5

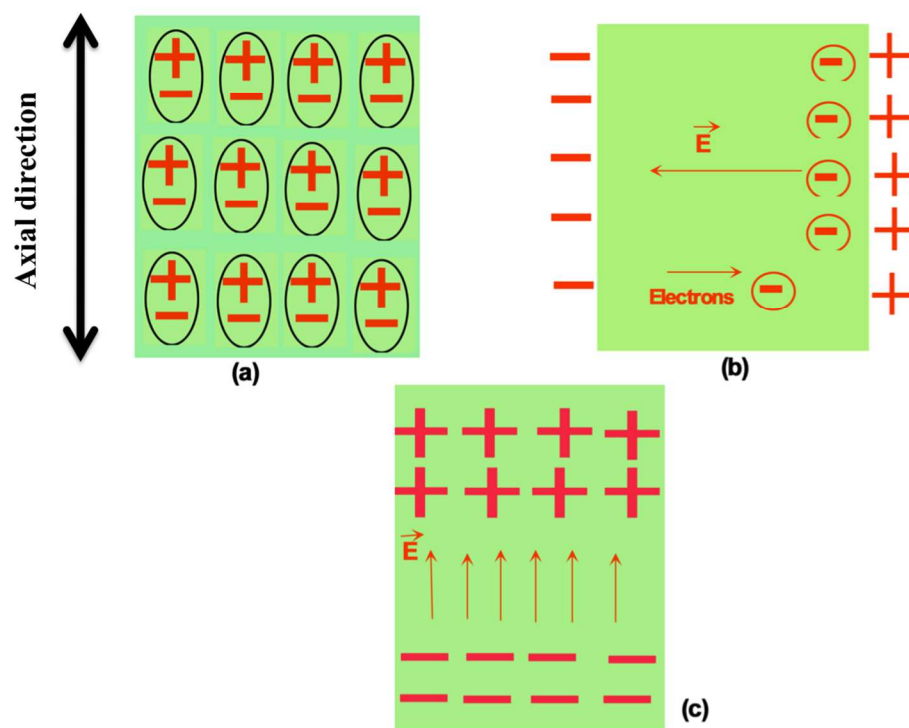


Fig. 6

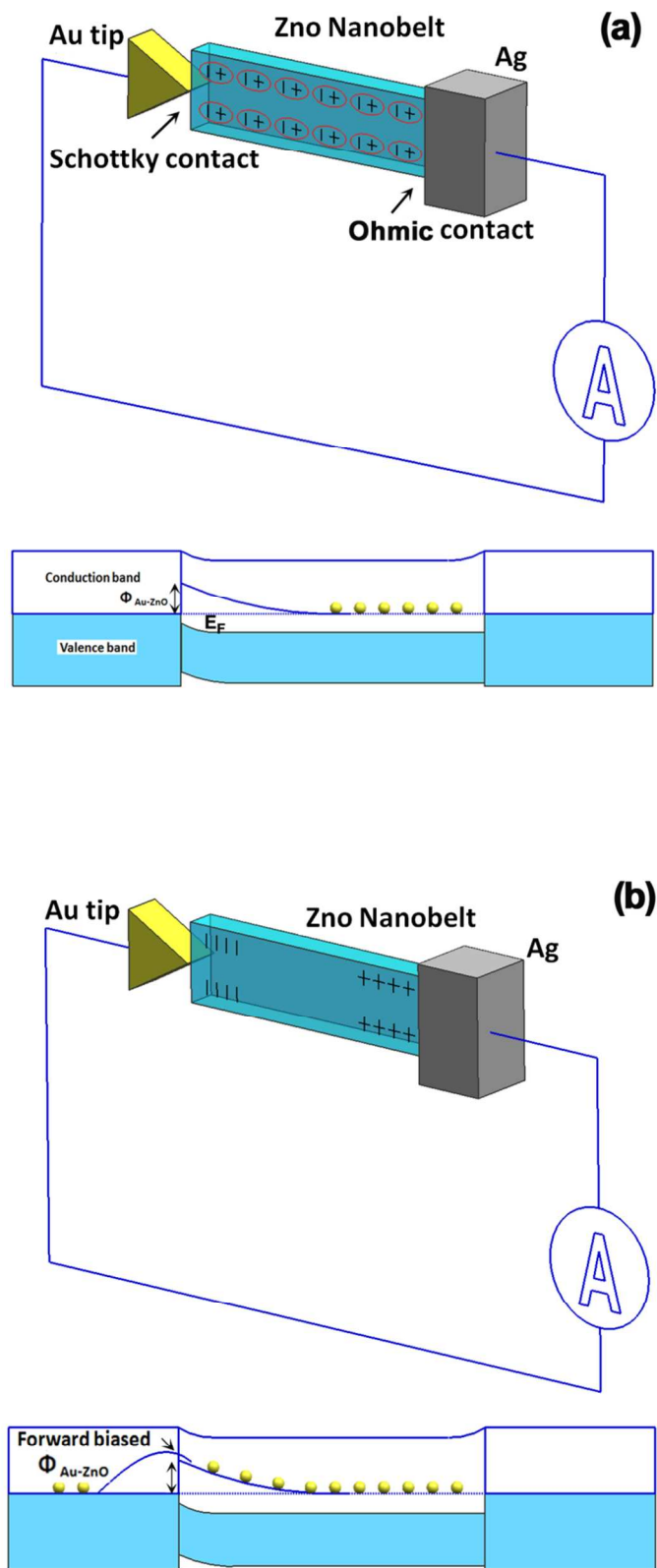


Fig. 7